

High-Voltage Schottky Rectifier, 10A/100V



FEATURES

- 150°C T_J operation
- Lower power losses, high efficiency
- Low forward voltage drop
- High forward surge capability
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Solder bath temperature 275°C maximum, 10s, per JESD 22-B106 (for TO-220AC and ITO-220AC package)
- Compliant to RoHS

TYPICAL APPLICATIONS

- Switching mode power supply
- DC-to-DC converters
- Freewheeling diodes
- Polarity protection.

MECHANICAL DATA

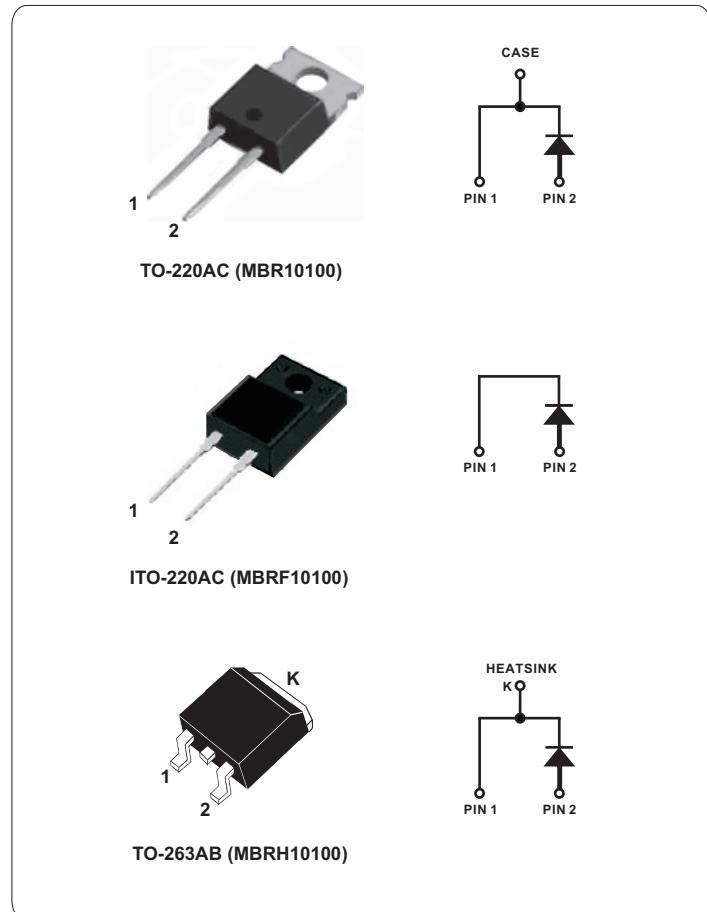
Case: TO-220AC, ITO-220AC, TO-263AB

Molding compound meets UL 94 V-O flammability rating

Terminals: Mat tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: As marked

Mounting Torque: 10 in-lbs maximum



PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	10A
V_{RRM}	100V
I_{FSM}	150A
V_F	0.65V
$T_{J\max.}$	150°C

MAJOR RATINGS AND CHARACTERISTICS ($T_c = 25^\circ C$ unless otherwise noted)			
PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	100	V
Working peak reverse voltage	V_{RWM}	100	V
Maximum DC blocking voltage	V_{DC}	100	V
Maximum average forward rectified output current at $T_c = 133^\circ C$	$I_{F(AV)}$	10	A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	150	A
Non-repetitive avalanche energy at $T_J = 25^\circ C$, $L = 60 \text{ mH}$	E_{AS}	130	mJ
Peak repetitive reverse current at $t_p = 2\mu s$, 1 kHz, $T_J = 38^\circ C \pm 2^\circ C$	I_{RRM}	0.5	A
Voltage rate of change (rated V_R)	dV/dt	10000	V/ μ s
Isolation voltage (ITO-220AC only) From terminal to heatsink $t = 1 \text{ min}$	V_{AC}	1500	V
Operating junction storage temperature range	$T_{J,T_{STG}}$	-65 to +150	°C

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ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	TEST CONDITIONS		SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage ⁽¹⁾	$I_F = 10\text{A}$	$T_c = 25^\circ\text{C}$	V_F	0.8	V
	$I_F = 10\text{A}$	$T_c = 125^\circ\text{C}$		0.65	
	$I_F = 20\text{A}$	$T_c = 125^\circ\text{C}$		0.75	
Maximum reverse current at working peak reverse voltage ⁽²⁾		$T_J = 25^\circ\text{C}$	I_R	100	μA
		$T_J = 100^\circ\text{C}$		6	mA

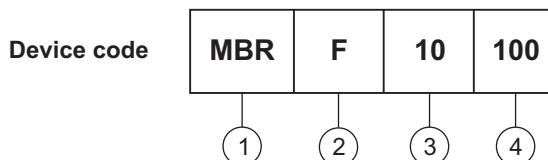
Notes

(1) Pulse test : 300 μs pulse width, 1% duty cycle

(2) Pulse test : Pulse width $\leq 40\text{ ms}$

THERMAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	MBR	MBRFX	MBRHXX	UNIT
Typical thermal resistance (junction-ambient)	$R_{\theta JA}$	60	-	60	$^\circ\text{C/W}$
Typical thermal resistance (junction-case)	$R_{\theta JC}$	2	3.5	2	
Approximate weight		2	2.5	2	g

Ordering Information Table



- 1 - Schottky MBR series
- 2 - Package outline, none for TO-220AC
 "F" for ITO-220AC (TO-220F)
 "H" for TO-263AB (D²PAK)
- 3 - Current rating, 10 = 10A
- 4 - Voltage rating, 100 = 100V

Fig.1 Forward current derating curve

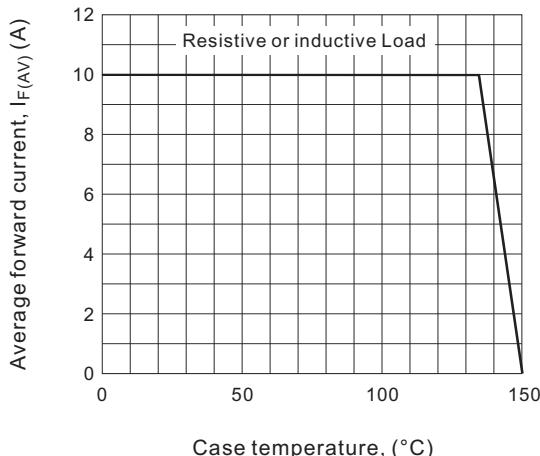


Fig.2 Maximum non-repetitive peak forward surge current

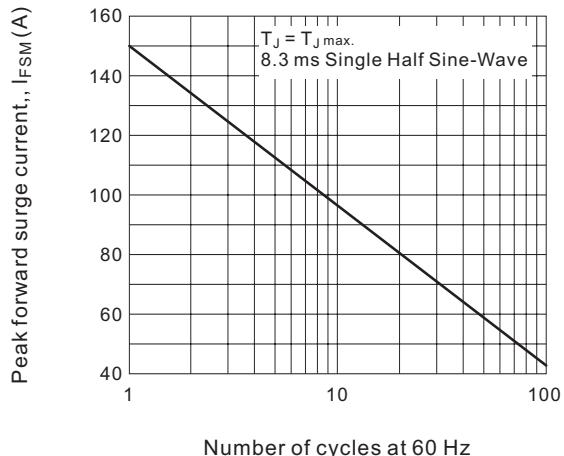
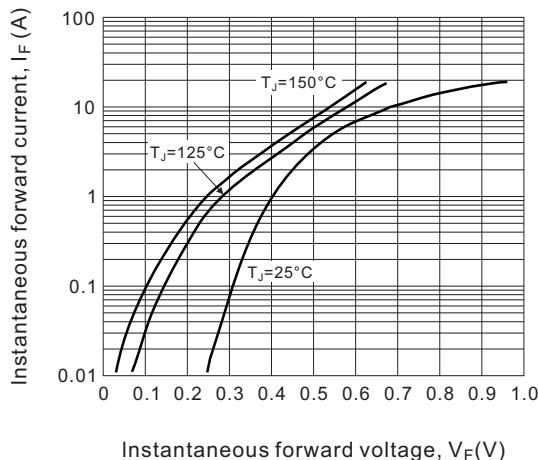
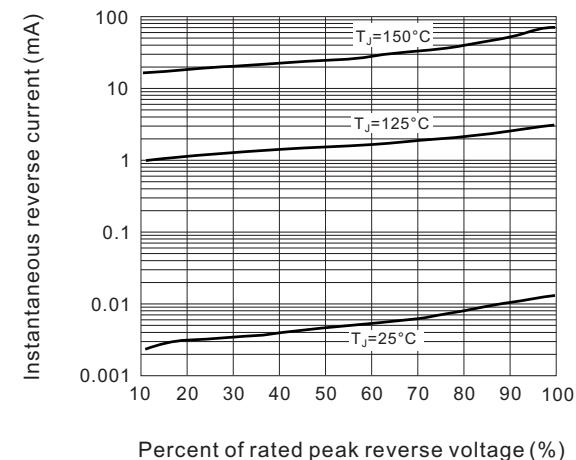
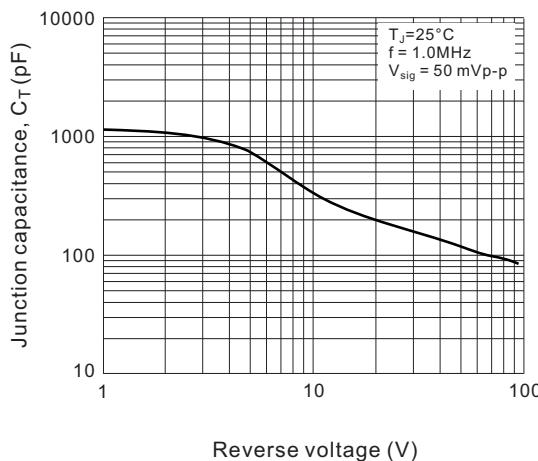
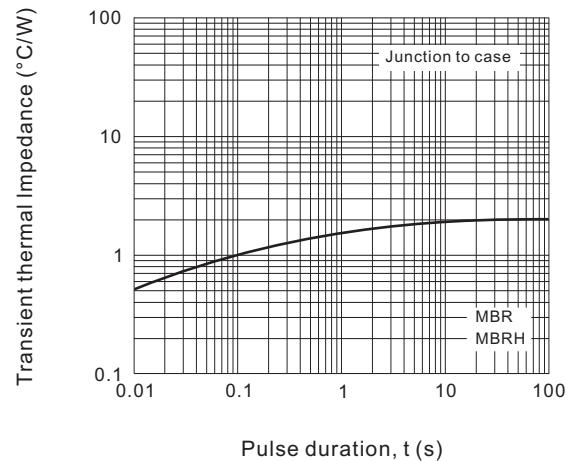
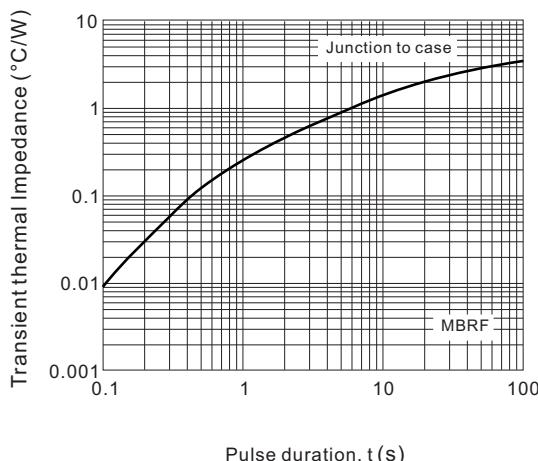


Fig.3 Typical instantaneous forward characteristics

Fig.4 Typical reverse characteristics

Fig.5 Typical junction capacitance

Fig.6 Typical transient thermal Impedance

Fig.7 Typical transient thermal Impedance


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